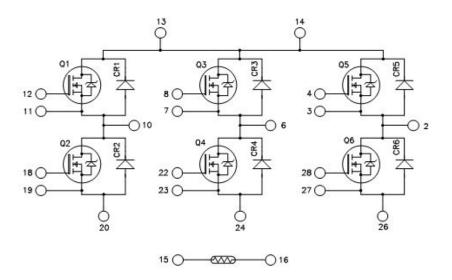
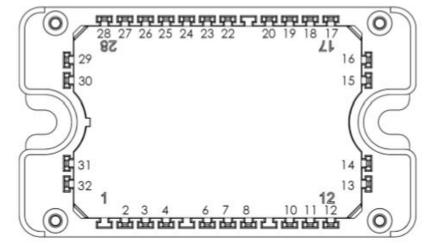
# MSCSM170TAM45CT3AG

## **Triple Phase Bridge SiC MOSFET Power Module**

#### **Product Overview**

The MSCSM170TAM45CT3AG device is a triple phase bridge 1700 V, 64 A silicon carbide (SiC) MOSFET power module.





**Note:** Pins 13/14 must be shorted together. Pins 20/24/26 must be shorted together to perform a three phase bridge.

All ratings at T<sub>J</sub> = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are key features of the MSCSM170TAM45CT3AG device:

- · SiC Power MOSFET
  - High speed switching
  - Low R<sub>DS(on)</sub>
  - Ultra low loss
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on VF
- · Very low stray inductance
- Kelvin source for easy drive
- · Internal thermistor for temperature monitoring
- · Aluminum nitride (AIN) substrate for improved thermal performance

#### **Benefits**

The following are the benefits of MSCSM170TAM45CT3AG device:

- · High efficiency converter
- Outstanding performance at high frequency operation
- · Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- Solderable terminals for power and signal for easy mounting of PCB
- · Low profile
- RoHS Compliant

### **Application**

The MSCSM170TAM45CT3AG device is designed for the following applications:

- · Welding converters
- · Switched mode power supplies
- · Uninterruptible power supplies
- EV motor and traction drive

### 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM170TAM45CT3AG device.

#### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM170TAM45CT3AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit	
V <sub>DSS</sub>	Drain-Source voltage		1700	V	
I <sub>D</sub>	Continuous drain current T <sub>C</sub> = 25 °C		64	А	
		T <sub>C</sub> = 80 °C			
I <sub>DM</sub>	Pulsed drain current		130		
V <sub>GS</sub>	Gate-Source voltage		-10/23	V	
R <sub>DS(on)</sub>	Drain-Source ON resistance		45	mΩ	
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	319	W	

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM170TAM45CT3AG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 1700 V		_	10	100	μΑ
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20 V	T <sub>J</sub> = 25 °C	_	35	45	mΩ
	resistance	I <sub>D</sub> = 30 A	T <sub>J</sub> = 175 °C	_	62	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ ; $I_D = 2.5 \text{ mA}$		1.8	3.2	_	V
I <sub>GSS</sub>	Gate–Source leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V		_	_	150	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM170TAM45CT3AG device.

**Table 1-3. Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V		_	3300	_	pF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 1000 V		_	150	_	
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	10	_	
$Q_g$	Total gate charge	V <sub>GS</sub> = -5 V/20 V		_	178	_	nC
Q <sub>gs</sub>	Gate-source charge	V <sub>Bus</sub> = 850 V		_	49	_	
$Q_{gd}$	Gate-drain charge	I <sub>D</sub> = 30 A		_	27	_	
T <sub>d(on)</sub>	Turn-on delay time	T <sub>J</sub> = 150 °C		_	24	_	ns
T <sub>r</sub>	Rise time	V <sub>GS</sub> = -5 V/20 V		_	17	_	
T <sub>d(off)</sub>	Turn-off delay time	V <sub>Bus</sub> = 900 V		_	35	_	
T <sub>f</sub>	Fall time	$I_D = 50 \text{ A}$ $R_{G(on)} = 4.7 \Omega$ $R_{G(off)} = 2.7 \Omega$			19	_	
E <sub>on</sub>	Turn-on energy	V <sub>GS</sub> = -5 V/20 V	T <sub>J</sub> = 150 °C	_	1.1	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus}$ = 900 V $I_{D}$ = 50 A $R_{G(on)}$ = 4.7 $\Omega$ $R_{G(off)}$ = 2.7 $\Omega$	T <sub>J</sub> = 150 °C	_	0.16	_	
R <sub>Gint</sub>	Internal gate resistance			_	0.85	_	Ω
R <sub>thJC</sub>	Junction-to-case therm	al resistance		_	_	0.47	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM170TAM45CT3AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V <sub>SD</sub>	Diode forward voltage	V <sub>GS</sub> = 0 V; I <sub>SD</sub> = 30 A	_	3.7	_	V
		$V_{GS} = -5 \text{ V}; I_{SD} = 30 \text{ A}$	_	3.9	_	
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 30 A; V <sub>GS</sub> = -5 V	_	27	_	ns
Q <sub>rr</sub>	Reverse recovery charge	$V_R = 900 \text{ V}; \text{ di}_F/\text{dt} = 1000 \text{ A/}\mu\text{s}$	_	650	_	nC
Irr	Reverse recovery current			46	_	А

#### 1.2 SiC Schottky Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics per SiC diode of MSCSM170TAM45CT3AG device.

Table 1-5. SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak repetitive reverse volta	age		_	_	1700	V
I <sub>RRM</sub>	Reverse leakage current	V <sub>R</sub> = 1700 V	T <sub>J</sub> = 25 °C	_	10	200	μA
			T <sub>J</sub> = 175 °C	_	150	_	
I <sub>F</sub>	DC forward current	_	T <sub>C</sub> = 125 °C	_	30	_	Α
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 30 A	T <sub>J</sub> = 25 °C	_	1.5	1.8	V
				_	2.3	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 900 V		_	230	_	nC
С	Total capacitance	al capacitance $f = 1 \text{ MHz}, V_R = 600 \text{ V}$ $f = 1 \text{ MHz}, V_R = 900 \text{ V}$		_	167	_	pF
				_	138	_	
R <sub>thJC</sub>	Junction-to-case thermal re	sistance		_	_	0.52	°C/W

#### 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM170TAM45CT3AG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristics			Min	Max	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			4000	_	٧
T <sub>J</sub>	Operating junction temperature range	Operating junction temperature range			175	°C
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage temperature range			-40	125	
T <sub>C</sub>	Operating case temperature			<b>-40</b>	125	
Torque	Mounting torque To heatsink M4			2	3	N.m
Wt	Package weight			_	110	g

The following table lists the temperature sensor NTC of the MSCSM170TAM45CT3AG device.

Table 1-7. Temperature Sensor NTC

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance at 25 °C	_	_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_	_	_	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K	_	_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

### 1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM170TAM45CT3AG device.

Figure 1-1. Maximum Thermal Impedance

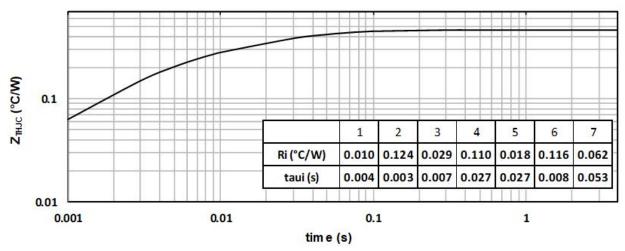


Figure 1-2. Output Characteristics,  $T_J = 25$  °C

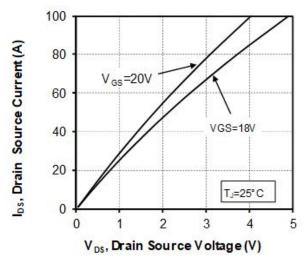


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C

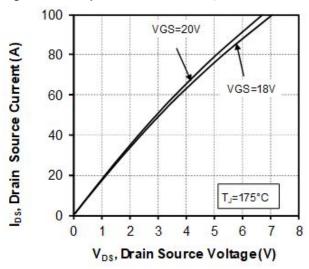


Figure 1-4. Normalized R<sub>DS(on)</sub> vs. Temperature

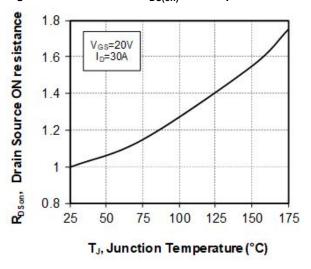


Figure 1-5. Transfer Characteristics

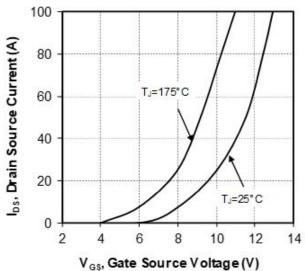


Figure 1-6. Switching Energy vs. Rg

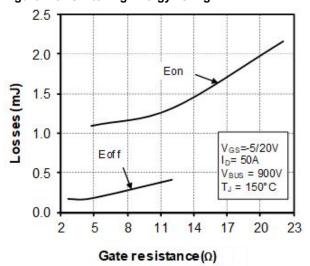


Figure 1-7. Switching Energy vs. Current

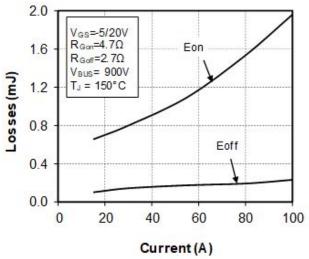


Figure 1-8. Capacitance vs. Drain Source Voltage

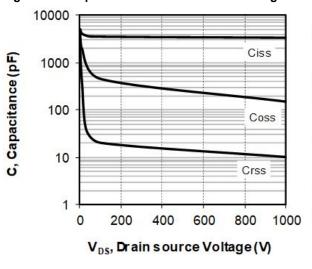
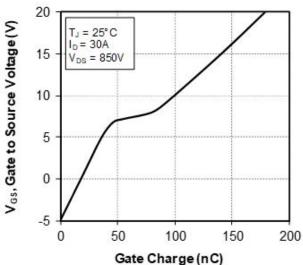


Figure 1-9. Gate Charge vs. Gate Source Voltage



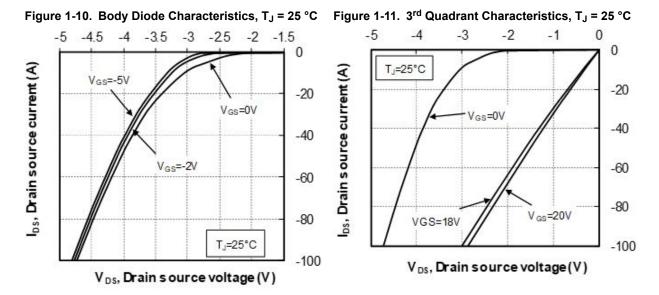
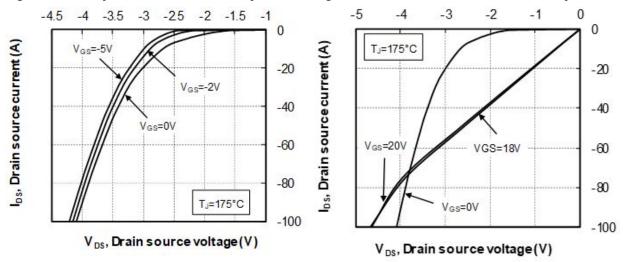


Figure 1-12. Body Diode Characteristics, T<sub>J</sub> = 175 °C Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 175 °C



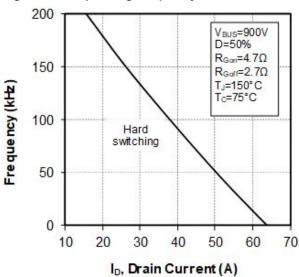


Figure 1-14. Operating Frequency vs Drain Current

#### 1.5 Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM170TAM45CT3AG device.

Figure 1-15. Maximum Thermal Impedance

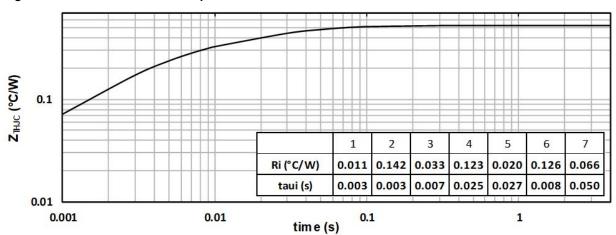


Figure 1-16. Forward Characteristics

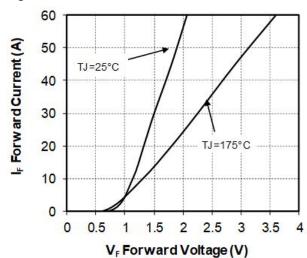
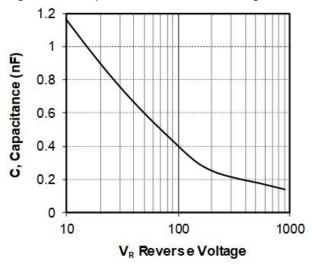


Figure 1-17. Capacitance vs. Reverse Voltage



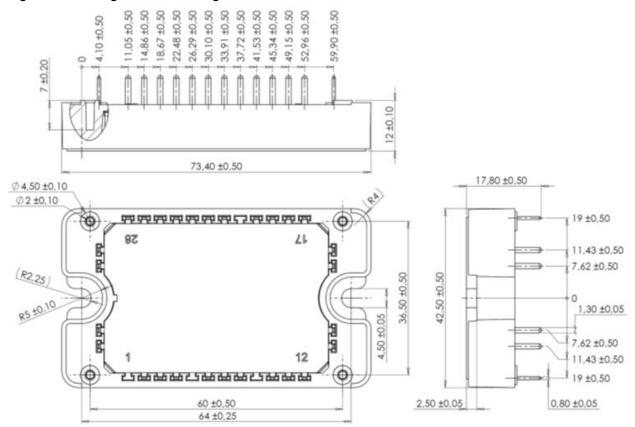
## 2. Package Specifications

The following section shows the package specification of the MSCSM170TAM45CT3AG device.

#### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM170TAM45CT3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information...

## MSCSM170TAM45CT3AG

**Revision History** 

# 3. Revision History

Revision	Date	Description
Α	04/2021	This is the first publication of this document.

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